

# UP04390

Silicon NPN epitaxial planar type (Tr1)  
Silicon PNP epitaxial planar type (Tr2)

For switching/digital circuits

## ■ Features

- Two elements incorporated into one package  
(Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

## ■ Basic Part Number

- UNR1114 + UNR1213

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

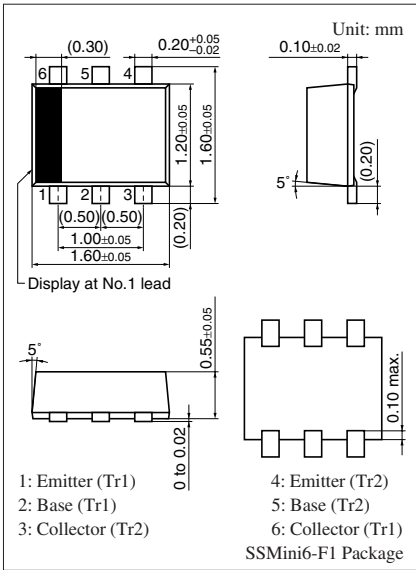
Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	50 V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50 V
	Collector current	$I_C$	100 mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-50 V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50 V
	Collector current	$I_C$	-100 mA
Overall	Total power dissipation	$P_T$	125 mW
	Junction temperature	$T_j$	125 $^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +125 $^\circ\text{C}$

## ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

- Tr1

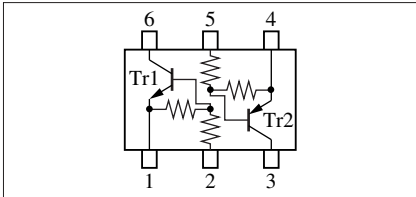
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}$ , $I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}$ , $I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{ V}$ , $I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 50 \text{ V}$ , $I_B = 0$			0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}$ , $I_C = 0$			0.1	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}$ , $I_C = 5 \text{ mA}$	80			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}$ , $I_B = 0.3 \text{ mA}$			0.25	V
Output voltage high level	$V_{OH}$	$V_{CC} = 5 \text{ V}$ , $V_B = 0.5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$	4.9			V
Output voltage low level	$V_{OL}$	$V_{CC} = 5 \text{ V}$ , $V_B = 3.5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$			0.2	V
Input resistance	$R_1$		-30%	4.7	+30%	$\text{k}\Omega$
Resistance ratio	$R_1/R_2$		0.8	1.0	1.2	—
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}$ , $I_E = -2 \text{ mA}$ , $f = 200\text{MHz}$		150		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



Marking Symbol: 3V

Internal Connection



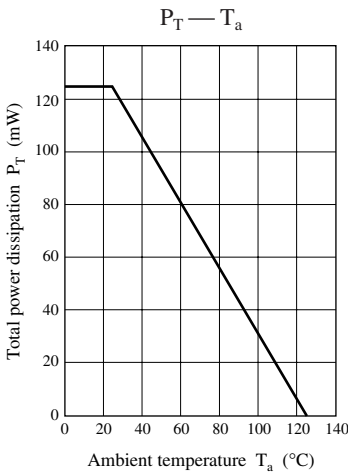
■ Electrical Characteristics (continued)  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr2

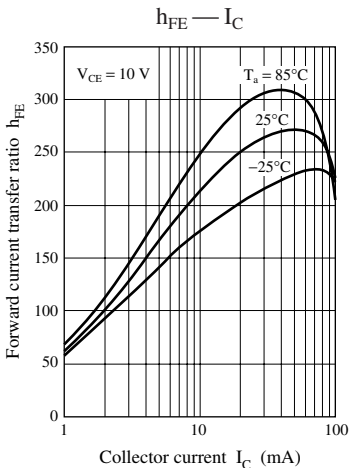
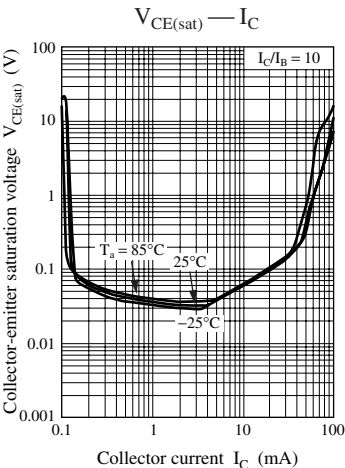
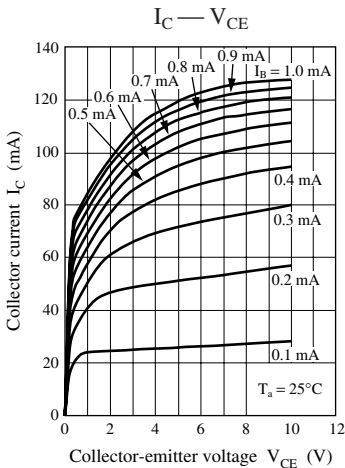
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10\ \mu\text{A}$ , $I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2\ \text{mA}$ , $I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -50\ \text{V}$ , $I_E = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -50\ \text{V}$ , $I_B = 0$			-0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -6\ \text{V}$ , $I_C = 0$			-0.2	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10\ \text{V}$ , $I_C = -5\ \text{mA}$	80			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\ \text{mA}$ , $I_B = -0.3\ \text{mA}$			-0.25	V
Output voltage high level	$V_{OH}$	$V_{CC} = -5\ \text{V}$ , $V_B = -0.5\ \text{V}$ , $R_L = 1\ \text{k}\Omega$	-4.9			V
Output voltage low level	$V_{OL}$	$V_{CC} = -5\ \text{V}$ , $V_B = -2.5\ \text{V}$ , $R_L = 1\ \text{k}\Omega$			-0.2	V
Input resistance	$R_i$		-30%	10	+30%	$\text{k}\Omega$
Resistance ratio	$R_1/R_2$		0.17	0.21	0.25	—
Transition frequency	$f_T$	$V_{CB} = -10\ \text{V}$ , $I_E = 1\ \text{mA}$ , $f = 200\text{MHz}$		80		MHz

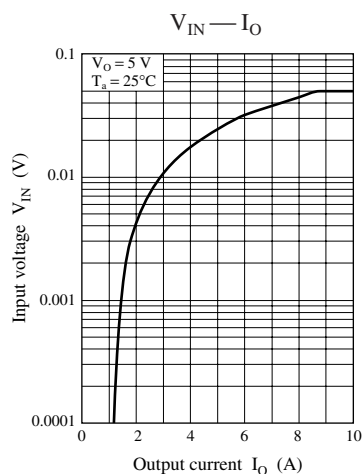
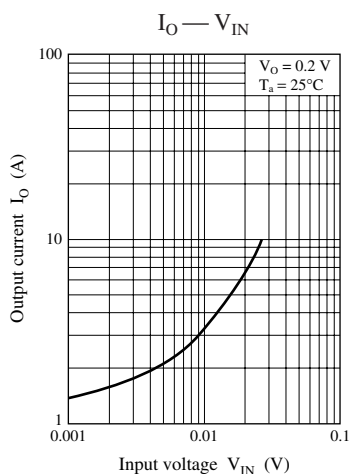
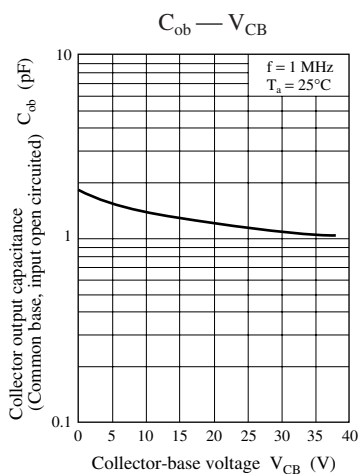
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

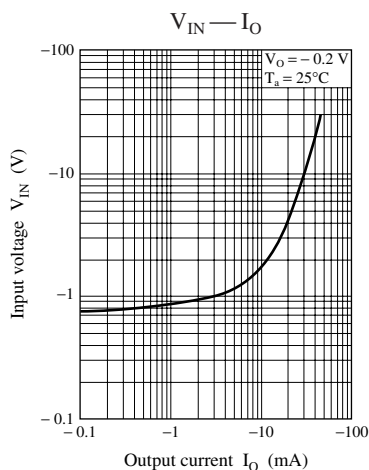
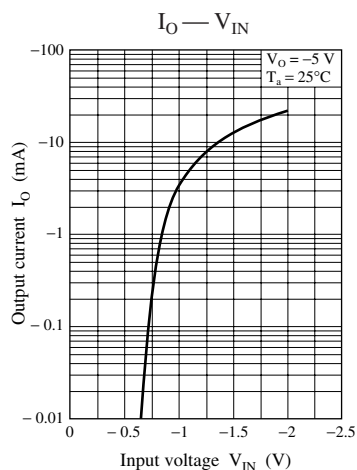
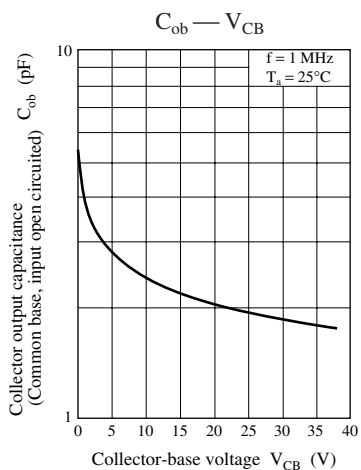
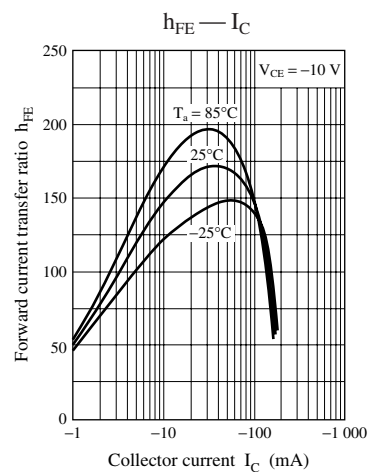
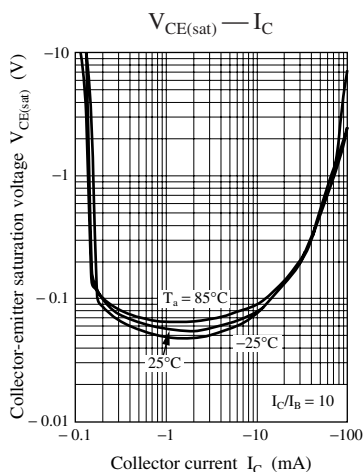
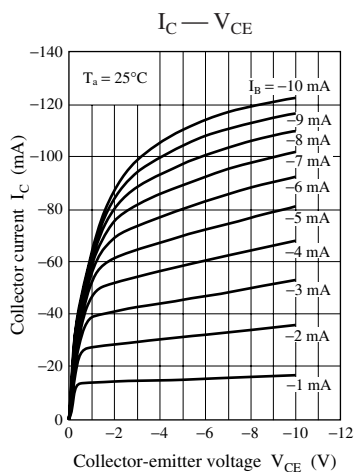


Characteristics charts of Tr1





## Characteristics charts of Tr2



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